



# STD95N4LF3

N-channel 40 V, 5.0 mΩ typ., 80 A STripFET™ III Power MOSFET in a DPAK package

Datasheet — production data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>	P <sub>D</sub>
STD95N4LF3	40 V	< 6.0 mΩ	80 A <sup>(1)</sup>	110 W

1. Value limited by wire bonding

- 100% avalanche tested
- Logic level drive

## Applications

- Switching application
  - Automotive

## Description

This device is an N-channel enhancement mode Power MOSFET produced using STMicroelectronics' STripFET™ III technology, which is specifically designed to minimize on-resistance and gate charge to provide superior switching performance.

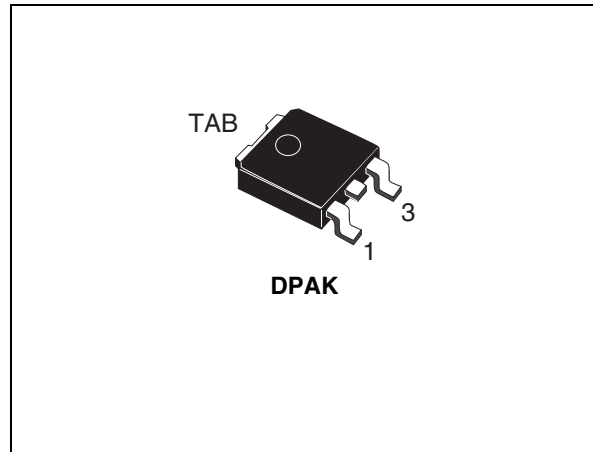


Figure 1. Internal schematic diagram

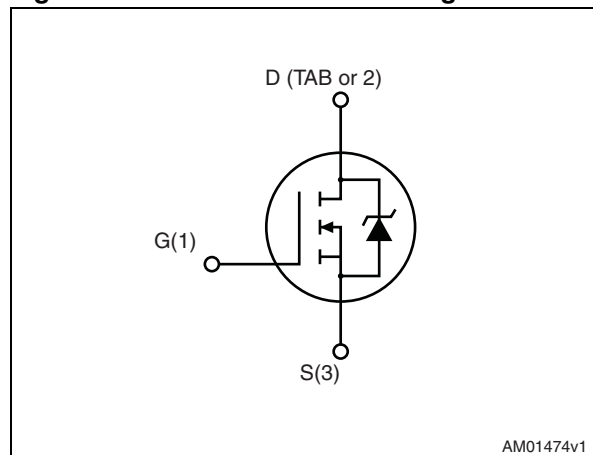


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD95N4LF3	95N4LF3	DPAK	Tape and reel

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 16$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	65	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
	Derating factor	0.73	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	8	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	400	mJ
$T_j$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

- Value limited by wire bonding
- Pulse width limited by safe operating area
- $I_{SD} \leq 80\text{ A}$ ,  $di/dt \leq 40\text{ A}/\mu\text{s}$ ,  $V_{DS} \leq V_{(BR)DSS}$ ,  $T_j \leq T_{JMAX}$
- Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 40\text{ A}$ ,  $V_{DD} = 35\text{ V}$  [Figure 16](#) and [Figure 17](#)

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.36	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50	$^\circ\text{C}/\text{W}$

- When mounted on 1inch<sup>2</sup> FR-4 2Oz Cu board

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	40			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 40\ \text{V}$ $V_{DS} = 40\ \text{V}$ , $T_C = 125\text{ °C}$			10 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 16\ \text{V}$			$\pm 200$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 40\ \text{A}$ $V_{GS} = 5\ \text{V}$ , $I_D = 40\ \text{A}$		5.0	6.0 9.0	$\text{m}\Omega$ $\text{m}\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\ \text{V}$ , $f = 1\ \text{MHz}$ , $V_{GS} = 0$	-	2500		pF
$C_{oss}$	Output capacitance			560		pF
$C_{rss}$	Reverse transfer capacitance			50		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\ \text{V}$ , $I_D = 40\ \text{A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\ \text{V}$ (see <a href="#">Figure 13</a> and <a href="#">Figure 18</a> )	-	7.5		ns
$t_r$	Rise time			45		ns
$t_{d(off)}$	Turn-off delay time			45		ns
$t_f$	Fall time			11		ns
$Q_g$	Total gate charge	$V_{DD} = 20\ \text{V}$ , $I_D = 80\ \text{A}$ , $V_{GS} = 10\ \text{V}$ (see <a href="#">Figure 14</a> )	-	50	70	nC
$Q_{gs}$	Gate-source charge			7		nC
$Q_{gd}$	Gate-drain charge			9.5		nC

**Table 6. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 20\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 15</a> and <a href="#">Figure 19</a> )	-	40 55 3		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

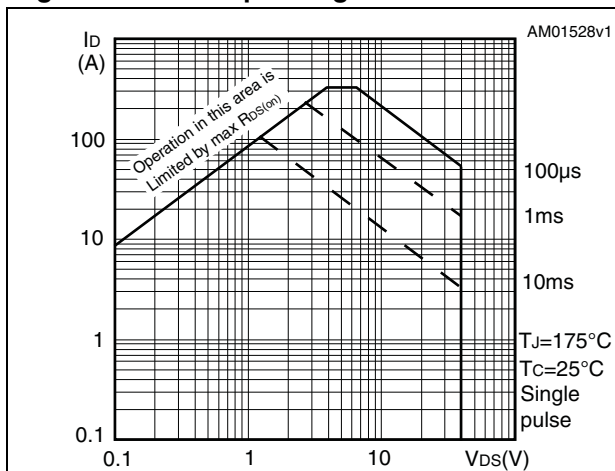


Figure 3. Thermal impedance

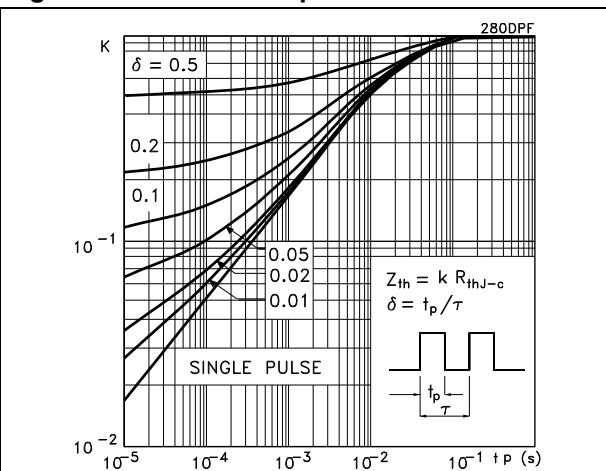


Figure 4. Output characteristics

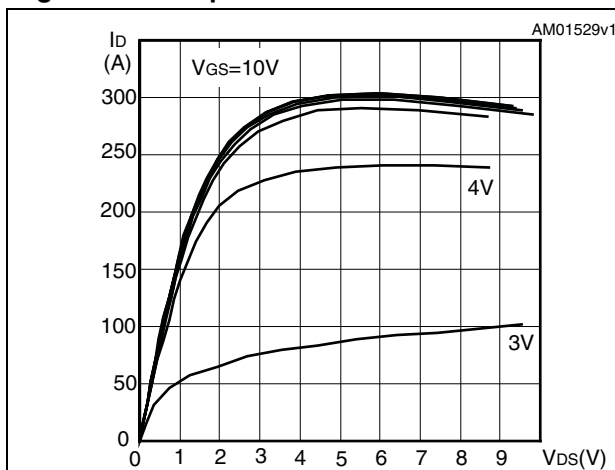


Figure 5. Transfer characteristics

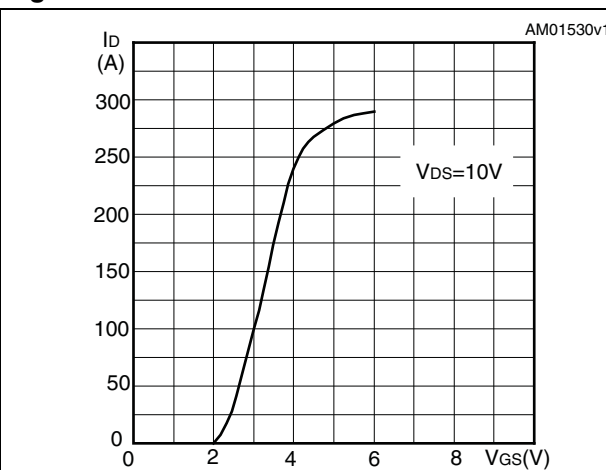


Figure 6. Static drain-source on-resistance

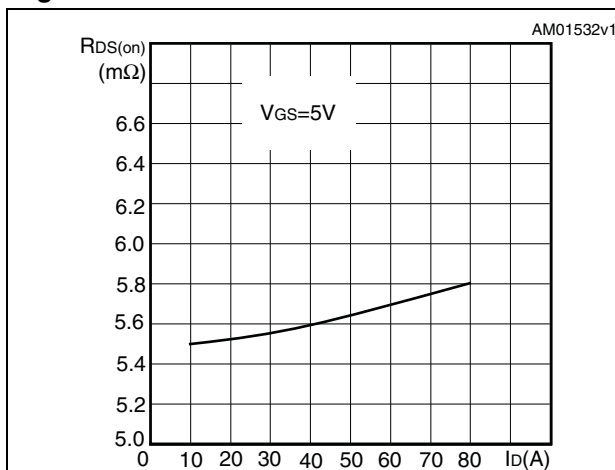


Figure 7. Normalized BV<sub>DSS</sub> vs temperature

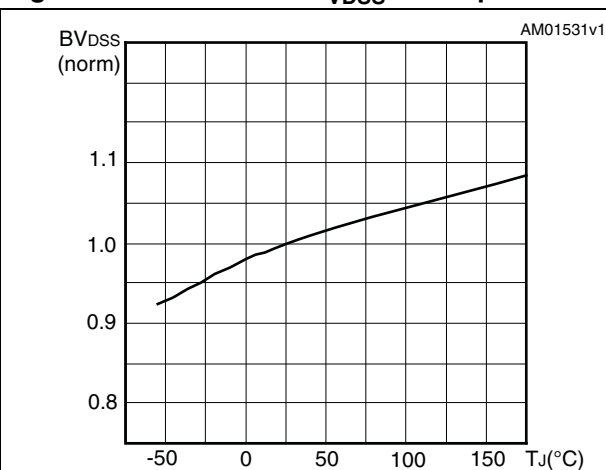


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

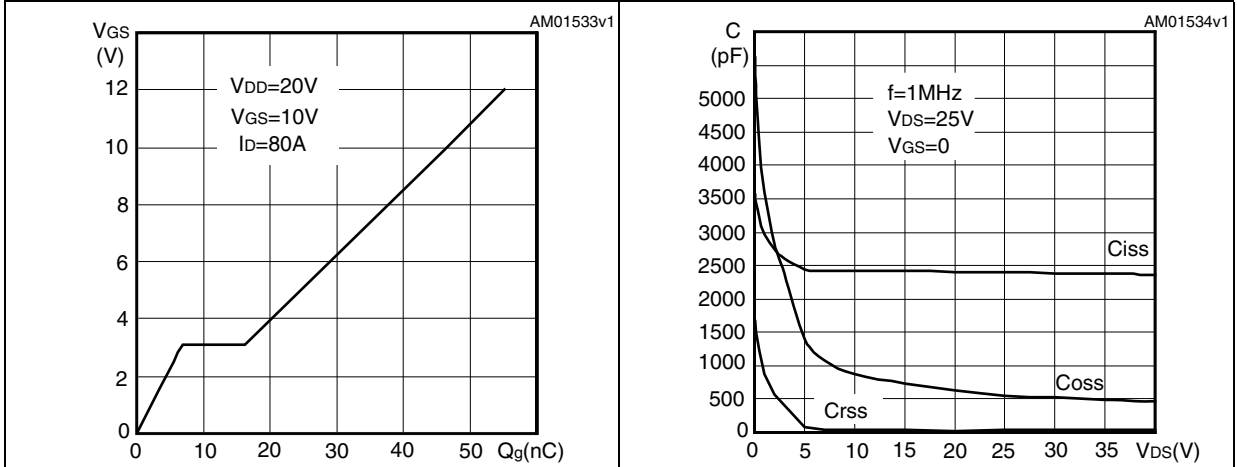


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

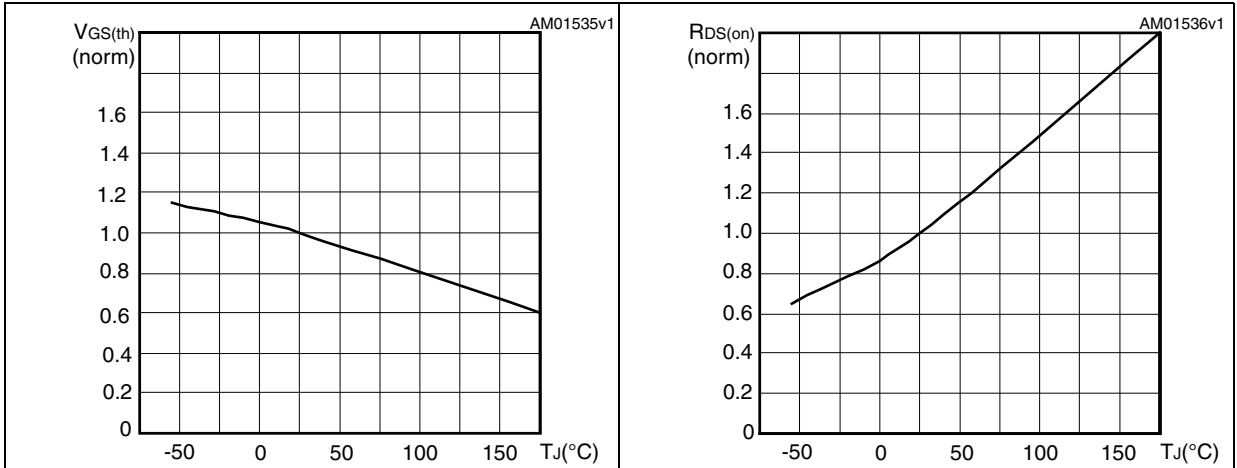
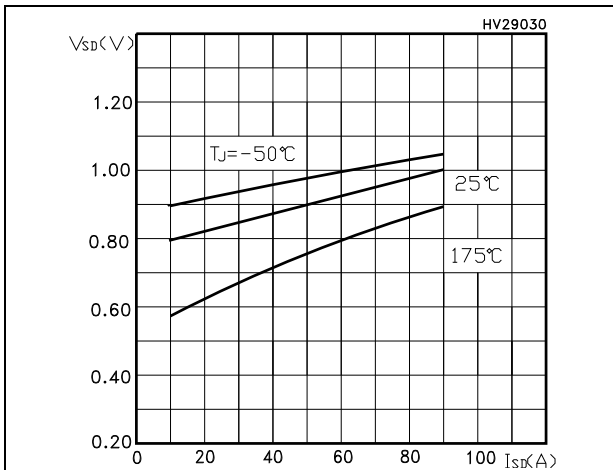


Figure 12. Source-drain diode forward characteristics



### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



AM01468v1

**Figure 14. Gate charge test circuit**



AM01469v1

**Figure 15. Test circuit for inductive load switching and diode recovery times**



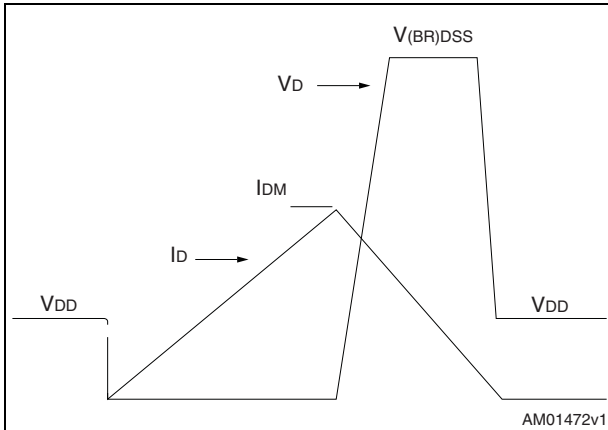
AM01470v1

**Figure 16. Unclamped inductive load test circuit**



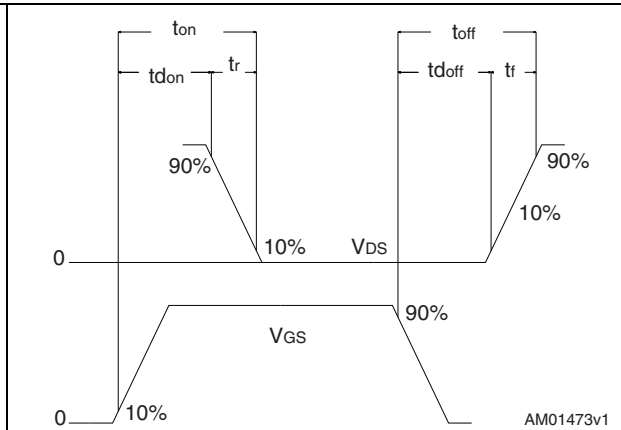
AM01471v1

**Figure 17. Unclamped inductive waveform**



AM01472v1

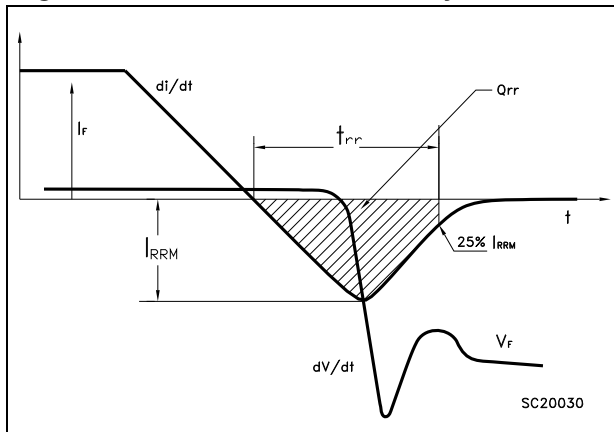
**Figure 18. Switching time waveform**



AM01473v1



Figure 19. Diode reverse recovery waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 7. DPAK (TO-252) mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 20. DPAK (TO-252) drawing

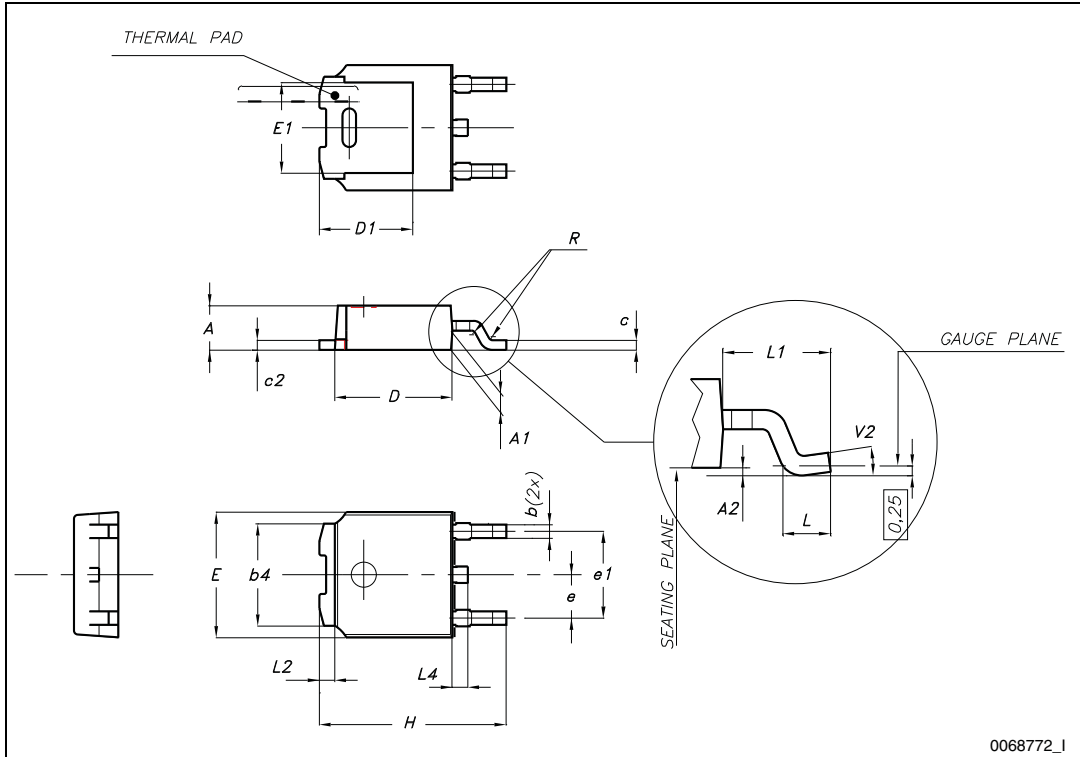
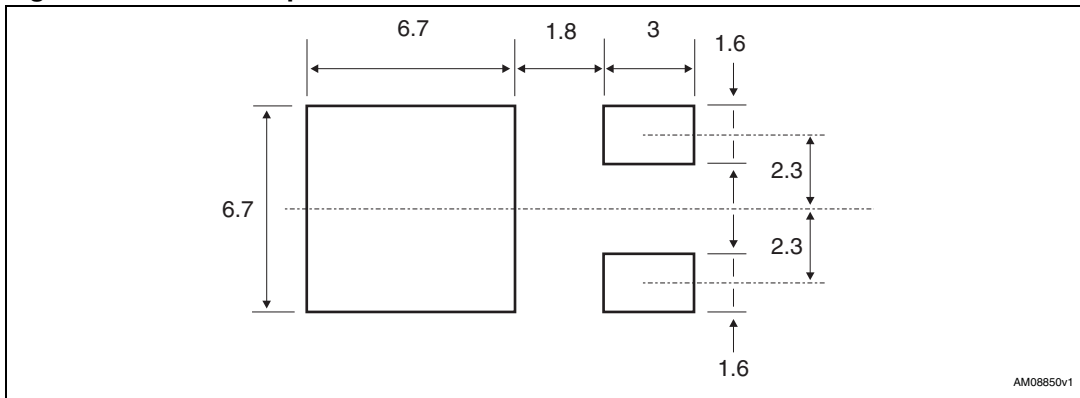


Figure 21. DPAK footprint<sup>(a)</sup>



a. All dimensions are in millimeters

## 5 Packing mechanical data

**Table 8. DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 22. Tape for DPAK (TO-252)

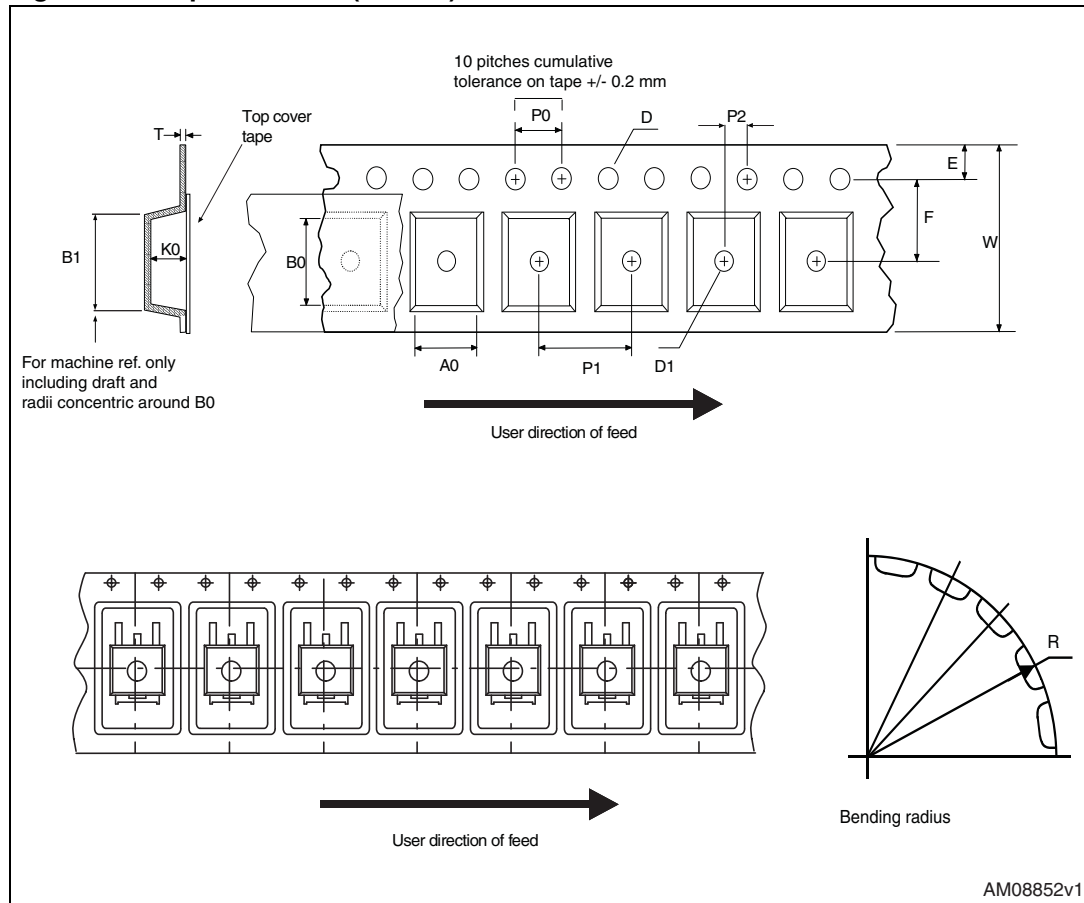
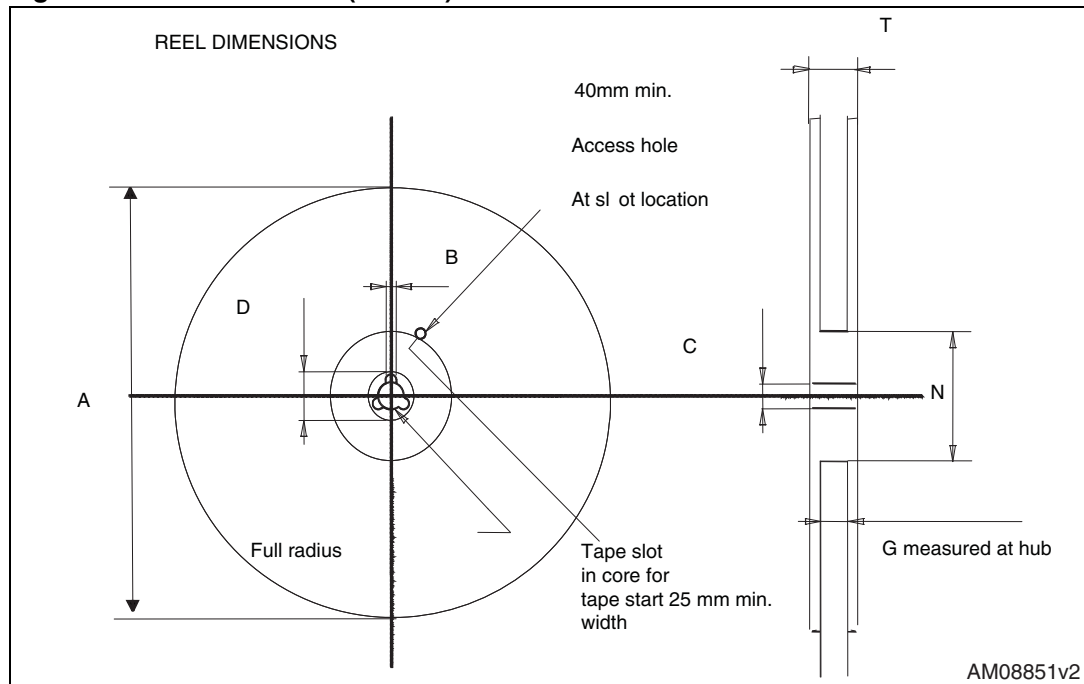


Figure 23. Reel for DPAK (TO-252)



## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
11-Feb-2009	1	First release
23-Jul-2009	2	Marking on device summary has been corrected.
13-Jul-2012	3	Updated title on the cover page. Minor text changes. Updated <i>Section 4: Package mechanical data</i> and <i>Section 5: Packing mechanical data</i> .

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